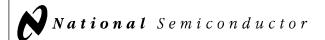
150 μV

10 fA

130 dB



LMC6082 Precision CMOS Dual Operational Amplifier

General Description

The LMC6082 is a precision dual low offset voltage operational amplifier, capable of single supply operation. Performance characteristics include ultra low input bias current, high voltage gain, rail-to-rail output swing, and an input common mode voltage range that includes ground. These features, plus its low offset voltage, make the LMC6082 ideally suited for precision circuit applications.

Other applications using the LMC6082 include precision fullwave rectifiers, integrators, references, and sample-andhold circuits.

This device is built with National's advanced Double-Poly Silicon-Gate CMOS process.

For designs with more critical power demands, see the LMC6062 precision dual micropower operational amplifier.

■ Photodiode and infrared detector preamplifier

■ Instrumentation amplifier

- Transducer amplifiers

■ Low offset voltage

■ High voltage gain

Applications

■ Ultra low input bias current

■ Improved latchup immunity

- Medical instrumentation
- D/A converter
- Charge amplifier for piezoelectric transducers

Features (Typical unless otherwise stated)

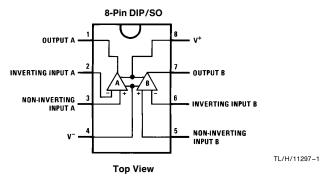
■ Output swing to within 20 mV of supply rail, 100k load

■ Operates from 4.5V to 15V single supply

■ Input common-mode range includes V⁻

PATENT PENDING

Connection Diagram



Ordering Information

	Temperatu	NSC	Transport		
Package	Military -55°C to +125°C	Industrial -40°C to +85°C	Drawing	Media	
8-Pin Molded DIP	LMC6082AMN	LMC6082AIN LMC6082IN	N08E	Rail	
8-Pin Small Outline		LMC6082AIM LMC6082IM	M08A	Rail Tape and Reel	

For MIL-STD-883C qualified products, please contact your local National Semiconductor Sales Office or Distributor for availability and specification information.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

 $\begin{array}{ll} \mbox{Differential Input Voltage} & \pm \mbox{Supply Voltage} \\ \mbox{Voltage at Input/Output Pin} & (V^+) + 0.3V, \\ & (V^-) - 0.3V \end{array}$

Supply Voltage (V $^+$ – V $^-$) 16V Output Short Circuit to V $^+$ (Note 11) Output Short Circuit to V $^-$ (Note 2) Lead Temperature (Soldering, 10 Sec.) 260°C

Storage Temp. Range -65°C to $+150^{\circ}\text{C}$ Junction Temperature 150°C

ESD Tolerance (Note 4) 2 kV

Operating Ratings (Note 1)

Temperature Range

Thermal Resistance ($\theta_{\rm JA}$) (Note 12)

8-Pin Molded DIP 115°C/W 8-Pin SO 193°C/W Power Dissipation (Note 10)

DC Electrical Characteristics

Unless otherwise specified, all limits guaranteed for $T_J=25^{\circ}C$. **Boldface** limits apply at the temperature extremes. $V^+=5V$, $V^-=0V$, $V_{CM}=1.5V$, $V_O=2.5V$ and $R_L>1M$ unless otherwise specified.

Symbol	Parameter	Condit	ions	Typ (Note 5)	LMC6082AM Limit (Note 6)	LMC6082AI Limit (Note 6)	LMC6082I Limit (Note 6)	Units
V _{OS}	Input Offset Voltage			150	350 1000	350 800	800 1300	μV Max
TCV _{OS}	Input Offset Voltage Average Drift			1.0				μV/°C
IB	Input Bias Current			0.010	100	4	4	pA Max
los	Input Offset Current			0.005	100	2	2	pA Max
R _{IN}	Input Resistance			>10				Tera Ω
CMRR	Common Mode Rejection Ratio	$0V \le V_{CM} \le 12.0V$ $V^+ = 15V$		85	75 72	75 72	66 63	dB Min
+PSRR	Positive Power Supply Rejection Ratio	$5V \le V^{+} \le 15V$ $V_{O} = 2.5V$		85	75 72	75 72	66 63	dB Min
-PSRR	Negative Power Supply Rejection Ratio	0V ≤ V ⁻ ≤ −10V		94	84 81	84 81	74 71	dB Min
OIVI	Input Common-Mode Voltage Range	$V^+ = 5V$ and 15V for CMRR ≥ 60 dB		-0.4	-0.1 O	-0.1 O	-0.1 O	V Max
				V ⁺ - 1.9	V ⁺ - 2.3 V ⁺ - 2.6	$V^+ - 2.3$ $V^+ - 2.5$	$V^+ - 2.3$ $V^+ - 2.5$	V Min
Av	Large Signal Voltage Gain	$R_L = 2 k\Omega$ (Note 7)	Sourcing	1400	400 300	400 300	300 200	V/mV Min
			Sinking	350	180 70	180 100	90 60	V/mV Min
		$R_L = 600\Omega$ (Note 7)	Sourcing	1200	400 150	400 150	200 80	V/mV Min
			Sinking	150	100 35	100 50	70 35	V/mV Min

DC Electrical Characteristics (Continued) Unless otherwise specified, all limits guaranteed for $T_J=25^{\circ}\text{C}$. **Boldface** limits apply at the temperature extremes. $V^+=5V$, $V^-=0V$, $V_{\text{CM}}=1.5V$, $V_{\text{O}}=2.5V$ and $R_{\text{L}}>1M$ unless otherwise specified.

Symbol	Parameter	Conditions	Typ (Note 5)	LMC6082AM Limit (Note 6)	LMC6082AI Limit (Note 6)	LMC6082I Limit (Note 6)	Units
Vo	Output Swing	$V^{+} = 5V$ $R_L = 2 k\Omega \text{ to } 2.5V$	4.87	4.80 4.70	4.80 4.73	4.75 4.67	V Min
			0.10	0.13 0.19	0.13 0.17	0.20 0.24	V Max
		$V^{+} = 5V$ $R_{L} = 600\Omega \text{ to } 2.5V$	4.61	4.50 4.24	4.50 4.31	4.40 4.21	V Min
			0.30	0.40 0.63	0.40 0.50	0.50 0.63	V Max
		$V^+ = 15V$ $R_L = 2 k\Omega$ to 7.5V	14.63	14.50 14.30	14.50 14.34	14.37 14.25	V Min
			0.26	0.35 0.48	0.35 0.45	0.44 0.56	V Max
		$V^{+} = 15V$ $R_{L} = 600\Omega$ to 7.5V	13.90	13.35 12.80	13.35 12.86	12.92 12.44	V Min
			0.79	1.16 1.42	1.16 1.32	1.33 1.58	V Max
lo	Output Current V+ = 5V	Sourcing, V _O = 0V	22	16 8	16 10	13 8	mA Min
		Sinking, V _O = 5V	21	16 11	16 13	13 10	mA Min
Io	Output Current V+ = 15V	Sourcing, V _O = 0V	30	28 18	28 22	23 18	mA Min
		Sinking, V _O = 13V (Note 11)	34	28 19	28 22	23 18	mA Min
IS	Supply Current	Both Amplifiers $V^+ = +5V$, $V_O = 1.5V$	0.9	1.5 1.8	1.5 1.8	1.5 1.8	mA Max
		Both Amplifiers V ⁺ = +15V, V _O = 7.5V	1.1	1.7 2	1.7 2	1.7 2	mA Max

AC Electrical Characteristics

Unless otherwise specified, all limits guaranteed for $T_J=25^{\circ}\text{C}$, **Boldface** limits apply at the temperature extremes. $V^+=5V$, $V^-=0V$, $V_{\text{CM}}=1.5V$, $V_{\text{O}}=2.5V$ and $R_L>1M$ unless otherwise specified.

Symbol	Parameter	Conditions	Typ (Note 5)	LMC6082AM Limit (Note 6)	LMC6082AI Limit (Note 6)	LMC6082I Limit (Note 6)	Units
SR	Slew Rate	(Note 8)	1.5	0.8 0.5	0.8 0.6	0.8 0.6	V/μs Min
GBW	Gain-Bandwidth Product		1.3				MHz
φ _m	Phase Margin		50				Deg
	Amp-to-Amp Isolation	(Note 9)	140				dB
e _n	Input-Referred Voltage Noise	F = 1 kHz	22				nV∕√ Hz
in	Input-Referred Current Noise	F = 1 kHz	0.0002				pA/√ Hz
T.H.D.	Total Harmonic Distortion	$\begin{aligned} F &= 10 \text{ kHz}, A_V = -10 \\ R_L &= 2 \text{ k}\Omega, V_O = 8 \text{ V}_{PP} \\ &\pm 5 \text{V Supply} \end{aligned}$	0.01				%

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed.

Note 2: Applies to both single-supply and split-supply operation. Continuous short circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of ±30 mA over long term may adversely affect reliability.

Note 3: The maximum power dissipation is a function of $T_{J(Max)}$, θ_{JA} , and T_A . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(Max)} - T_A) / \theta_{JA}$.

Note 4: Human body model, 1.5 $k\Omega$ in series with 100 pF.

Note 5: Typical values represent the most likely parametric norm.

Note 6: All limits are guaranteed by testing or statistical analysis.

Note 7: V $^+$ = 15V, V $_{CM}$ = 7.5V and R $_{L}$ connected to 7.5V. For Sourcing tests, 7.5V \leq V $_{O}$ \leq 11.5V. For Sinking tests, 2.5V \leq V $_{O}$ \leq 7.5V.

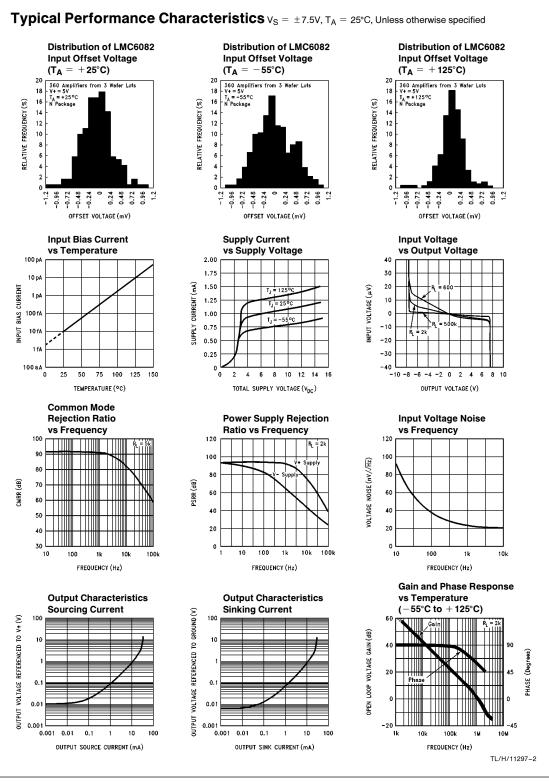
Note 8: V+ = 15V. Connected as Voltage Follower with 10V step input. Number specified is the slower of the positive and negative slew rates.

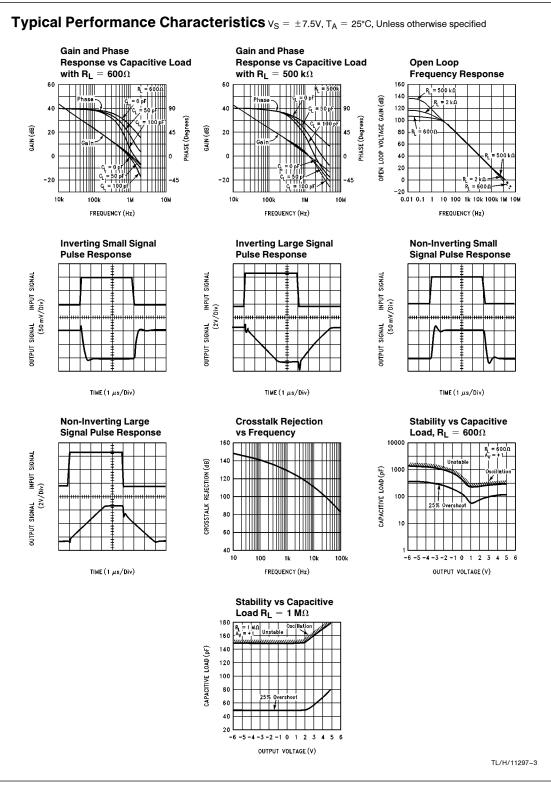
Note 9: Input referred V $^+$ = 15V and R_L = 100 k Ω connected to 7.5V. Each amp excited in turm with 1 kHz to produce V_O = 12 V_{PP}.

Note 10: For operating at elevated temperatures the device must be derated based on the thermal resistance θ_{JA} with $P_D = (T_J - T_A)/\theta_{JA}$. All numbers apply for packages soldered directly into a PC board.

 $\textbf{Note 11:} \ \ \text{Do not connect output to V}^+, \ \text{when V}^+ \ \text{is greater than 13V or reliability will be adversely affected}.$

Note 12: All numbers apply for packages soldered directly into a PC board.





Applications Hints

AMPLIFIER TOPOLOGY

The LMC6082 incorporates a novel op-amp design topology that enables it to maintain rail to rail output swing even when driving a large load. Instead of relying on a push-pull unity gain output buffer stage, the output stage is taken directly from the internal integrator, which provides both low output impedance and large gain. Special feed-forward compensation design techniques are incorporated to maintain stability over a wider range of operating conditions than traditional micropower op-amps. These features make the LMC6082 both easier to design with, and provide higher speed than products typically found in this ultra-low power class.

COMPENSATING FOR INPUT CAPACITANCE

It is quite common to use large values of feedback resistance for amplifiers with ultra-low input current, like the

Although the LMC6082 is highly stable over a wide range of operating conditions, certain precautions must be met to achieve the desired pulse response when a large feedback resistor is used. Large feedback resistors and even small values of input capacitance, due to transducers, photodiodes, and circuit board parasitics, reduce phase margins.

When high input impedances are demanded, guarding of the LMC6082 is suggested. Guarding input lines will not only reduce leakage, but lowers stray input capacitance as well. (See Printed-Circuit-Board Layout for High Impedance Work).

The effect of input capacitance can be compensated for by adding a capacitor, C_f, around the feedback resistors (as in Figure 1) such that:

$$\frac{1}{2\pi R_1 C_{IN}} \ge \frac{1}{2\pi R_2 C_f}$$
 or
$$R_1 C_{IN} \le R_2 C_f$$

Since it is often difficult to know the exact value of CIN, Cf can be experimentally adjusted so that the desired pulse response is achieved. Refer to the LMC660 and LMC662 for a more detailed discussion on compensating for input capacitance.

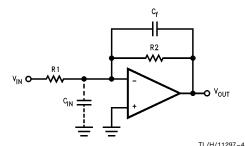
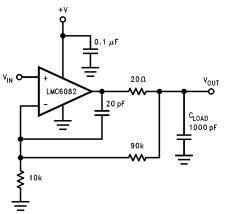


FIGURE 1. Cancelling the Effect of Input Capacitance **CAPACITIVE LOAD TOLERANCE**

All rail-to-rail output swing operational amplifiers have voltage gain in the output stage. A compensation capacitor is normally included in this integrator stage. The frequency location of the dominant pole is affected by the resistive load on the amplifier. Capacitive load driving capability can be optimized by using an appropriate resistive load in parallel with the capacitive load (see typical curves).

Direct capacitive loading will reduce the phase margin of many op-amps. A pole in the feedback loop is created by the combination of the op-amp's output impedance and the capacitive load. This pole induces phase lag at the unitygain crossover frequency of the amplifier resulting in either an oscillatory or underdamped pulse response. With a few external components, op amps can easily indirectly drive capacitive loads, as shown in Figure 2a.



TI /H/11297-5

FIGURE 2a. LMC6082 Noninverting Gain of 10 Amplifier, **Compensated to Handle Capacitive Loads**

In the circuit of Figure 2a, R1 and C1 serve to counteract the loss of phase margin by feeding the high frequency component of the output signal back to the amplifier's inverting input, thereby preserving phase margin in the overall feedback loop.

Capacitive load driving capability is enhanced by using a pull up resistor to V^+ (Figure 2b). Typically a pull up resistor conducting 500 µA or more will significantly improve capacitive load responses. The value of the pull up resistor must be determined based on the current sinking capability of the amplifier with respect to the desired output swing. Open loop gain of the amplifier can also be affected by the pull up resistor (see Electrical Characteristics).

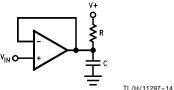


FIGURE 2b. Compensating for Large Capacitive Loads with a Pull Up Resistor

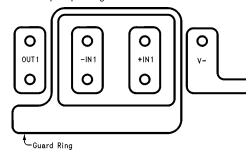
PRINTED-CIRCUIT-BOARD LAYOUT FOR HIGH-IMPEDANCE WORK

It is generally recognized that any circuit which must operate with less than 1000 pA of leakage current requires special layout of the PC board. When one wishes to take advantage of the ultra-low bias current of the LMC6082, typically less than 10 fA, it is essential to have an excellent layout. Fortunately, the techniques of obtaining low leakages are quite simple. First, the user must not ignore the surface

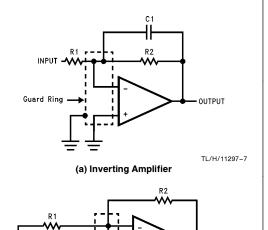
Applications Hints

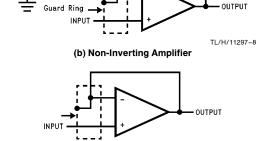
leakage of the PC board, even though it may sometimes appear acceptably low, because under conditions of high humidity or dust or contamination, the surface leakage will be appreciable.

To minimize the effect of any surface leakage, lay out a ring of foil completely surrounding the LMC6082's inputs and the terminals of capacitors, diodes, conductors, resistors, relay terminals, etc. connected to the op-amp's inputs, as in Figure 3. To have a significant effect, guard rings should be placed on both the top and bottom of the PC board. This PC foil must then be connected to a voltage which is at the same voltage as the amplifier inputs, since no leakage current can flow between two points at the same potential. For example, a PC board trace-to-pad resistance of $10^{12}\Omega$, which is normally considered a very large resistance, could leak 5 pA if the trace were a 5V bus adjacent to the pad of the input. This would cause a 100 times degradation from the LMC6082's actual performance. However, if a guard ring is held within 5 mV of the inputs, then even a resistance of $10^{11}\Omega$ would cause only 0.05 pA of leakage current. See Figures 4a, 4b, 4c for typical connections of guard rings for standard op-amp configurations.



 $$^{\rm TL/H/11297-6}$$ FIGURE 3. Example of Guard Ring in P.C. Board Layout





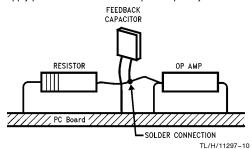
(c) Follower
FIGURE 4. Typical Connections of Guard Rings

TL/H/11297-9

The designer should be aware that when it is inappropriate to lay out a PC board for the sake of just a few circuits, there is another technique which is even better than a guard ring on a PC board: Don't insert the amplifier's input pin into the board at all, but bend it up in the air and use only air as an insulator. Air is an excellent insulator. In this case you may have to forego some of the advantages of PC board construction, but the advantages are sometimes well worth the effort of using point-to-point up-in-the-air wiring. See Figure 5.

Latchup

CMOS devices tend to be susceptible to latchup due to their internal parasitic SCR effects. The (I/O) input and output pins look similar to the gate of the SCR. There is a minimum current required to trigger the SCR gate lead. The LMC6062 and LMC6082 are designed to withstand 100 mA surge current on the I/O pins. Some resistive method should be used to isolate any capacitance from supplying excess current to the I/O pins. In addition, like an SCR, there is a minimum holding current for any latchup mode. Limiting current to the supply pins will also inhibit latchup susceptibility.



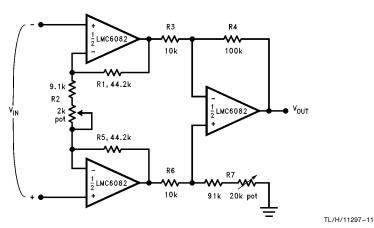
(Input pins are lifted out of PC board and soldered directly to components. All other pins connected to PC board).

Typical Single-Supply Applications $(V^{+} = 5.0 V_{DC})$

The extremely high input impedance, and low power consumption, of the LMC6082 make it ideal for applications that require battery-powered instrumentation amplifiers. Examples of these types of applications are hand-held pH probes, analytic medical instruments, magnetic field detectors, gas detectors, and silicon based pressure transducers.

Figure 6 shows an instrumentation amplifier that features high differential and common mode input resistance $(>10^{14}\Omega)$, 0.01% gain accuracy at A_V = 1000, excellent CMRR with 1 $k\Omega$ imbalance in bridge source resistance. Input current is less than 100 fA and offset drift is less than 2.5 $\mu\text{V}/^{\circ}\text{C.}$ R_{2} provides a simple means of adjusting gain over a wide range without degrading CMRR. R7 is an initial trim used to maximize CMRR without using super precision matched resistors. For good CMRR over temperature, low drift resistors should be used.

FIGURE 5. Air Wiring



If $\mathsf{R}_1\,=\,\mathsf{R}_5,\,\mathsf{R}_3\,=\,\mathsf{R}_6,$ and $\mathsf{R}_4\,=\,\mathsf{R}_7;$ then

$$\frac{v_{OUT}}{v_{IN}} = \frac{R_2 \, + \, 2\,R_1}{R_2} \times \frac{R_4}{R_3}$$

 $\therefore A_V \approx 100$ for circuit shown (R₂ = 9.822k).

FIGURE 6. Instrumentation Amplifier

Typical Single-Supply Applications (V $^+$ = 5.0 V_{DC})

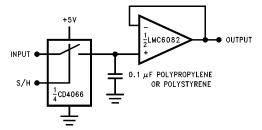


FIGURE 7. Low-Leakage Sample and Hold

TL/H/11297-12

TL/H/11297-13

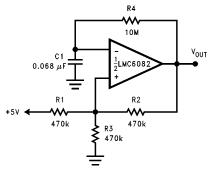
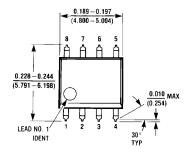
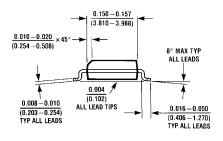
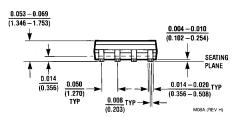


FIGURE 8. 1 Hz Square Wave Oscillator

Physical Dimensions inches (millimeters)

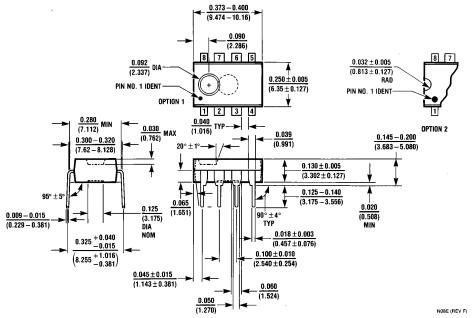






8-Pin Small Outline Package Order Number LMC6082AIM or LMC6082IM NS Package Number M08A

Physical Dimensions inches (millimeters) (Continued)



8-Pin Molded Dual-In-Line Package Order Number LMC6082AIN, LMC6082AMN or LMC6082IN NS Package Number N08E

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